09/889838 CLM 5-113-04

AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application:

LISTING OF CLAIMS:

Claims 1 to 14: (Canceled).

15. (Currently Amended) A method for etching a pattern in an etching body in accordance with a plasma, comprising the steps of:

coupling at least temporarily a high-frequency-pulsed high-frequency power into the etching body via an at least temporarily applied high-frequency a.c. voltage; and

modulating the coupled, high-frequency-pulsed high-frequency power is modulated at a low frequency;

wherein a mark-to-space ratio of the high-frequency-pulsed high-frequency power is between 1:2 and 1:100.

- 16. (Previously Presented) The method of claim 15, wherein: the etching pattern is a cut-out, the etching body is a silicon body, and the cut-outs are exactly defined by an etching mask in a lateral manner.
- 17. (Previously Presented) The method of claim 15, wherein the at least temporarily applied high-frequency a.c. voltage is provided by a high-frequency generator, the high-frequency generator generating a high-frequency carrier signal.
- 18. (Previously Presented) The method of claim 15, wherein the high-frequency-pulsed high-frequency power is pulsed at a frequency of 10 kHz to 500 kHz.
- 19. (Previously Presented) The m thod of claim 18, wherein the high-frequency-pulsed high-frequency power is pulsed at a frequency of 50 kHz to 200 kHz.

- 20. (Previously Present d) The method of claim 17, wherein the high-frequency carrier signal has a frequency of 1 MHz to 50 MHz.
- 21. (Currently Amended) The method of claim 20, wherein the high-frequency carrier signal has a frequency of 13.56 [[mHz]] MHz.
- 22. (Previously Presented) The method of claim 17, wherein the high-frequency generator generates a high-frequency power having an amplitude of 30 watts to 1200 watts.
- 23. (Previously Presented) The method of claim 22, wherein the high-frequency generator generates a high-frequency power having an amplitude of 50 watts to 500 watts.
- 24. (Previously Presented) The method of claim 15, wherein the high-frequency-power is coupled in the form of square-wave pulse.
- 25. (Currently Amended) The A method of claim 24 for etching a pattern in an etching body in accordance with a plasma, comprising the steps of:

coupling at least temporarily a high-frequency-pulsed high-frequency power into the etching body via an at least temporarily applied high-frequency a.c. voltage; and

modulating the coupled, high-frequency-pulsed high-frequency power at a low frequency,

wherein the high-frequency-pulsed high-frequency power is coupled in the form of square-wave pulses; and

wherein the square-wave pulses have a rise time of clock pulse edges of the square-wave pulses of less than 0.3 μs .

Claim 26: (Canceled).

27. (Currently Amended) The method of claim 26 15, wherein the mark-to-space ratio of the high-frequency-pulsed high-frequency pow r is between 1:2 and 1:19.

- 28. (Previously Presented) The method of claim 15, wherein a sequence of pulses of the high-frequency-pulsed power and pulse intervals corresponds to an average high-frequency power of 1 watt to 100 watts.
- 29. (Previously Presented) The method of claim 15, wherein the coupled, high-frequency-pulsed high-frequency power is periodically modulated using a low-frequency clocking.
- 30. (Previously Presented) The method of claim 15, wherein one of a low-frequency clocking and the low-frequency modulation is performed at a frequency of 10 Hz to 10000 Hz.
- 31. (Previously Presented) The method of claim 30, wherein the one of the low-frequency clocking and the low-frequency modulation is performed at a frequency of 50 Hz to 1000 Hz.
- 32. (Previously Presented) The method of claim 15, wherein one of a low-frequency clocking and the low-frequency modulation causes the coupled, high-frequency-pulsed high-frequency power to be periodically switched on and off.
- 33. (Previously Presented) The method of claim 15, wherein a mark-to-space ratio of a low-frequency clocking is between 4:1 and 1:4.
- 34. (Previously Presented) The method of claim 33, wherein the mark-to-space ratio of the low-frequency clocking is between 1:2 and 2:1.
- 35. (Currently Amended) The A method of claim 15 for etching a pattern in an etching body in accordance with a plasma, comprising the steps of:

coupling at least temporarily a high-frequency-pulsed high-frequency power into the etching body via an at least temporarily applied high-frequency a.c. voltage; and

modulating the coupled, high-frequency-pulsed high-frequency power at a low frequency,

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wherein a time-averaged value for the high-frequency-pulsed high-frequency pow r coupled into the etching body is between 1 watt and 30 watts.

36. (New) A method for etching a pattern in an etching body in accordance with a plasma, comprising the steps of:

coupling at least temporarily a high-frequency-pulsed high-frequency power into the etching body via an at least temporarily applied high-frequency a.c. voltage; and

modulating the coupled, high-frequency-pulsed high-frequency power at a low frequency;

wherein a time-averaged value for the high-frequency-pulsed high-frequency power coupled into the etching body is between 1 watt and 30 watts.

- 37. (New) The method of claim 36, wherein:
 the etching pattern is a cut-out,
 the etching body is a silicon body, and
 the cut-outs are exactly defined by an etching mask in a lateral manner.
- 38. (New) The method of claim 36, wherein the at least temporarily applied high-frequency a.c. voltage is provided by a high-frequency generator, the high-frequency generator generating a high-frequency carrier signal.
- 39. (New) The method of claim 36, wherein the high-frequency-pulsed high-frequency power is pulsed at a frequency of 10 kHz to 500 kHz.
- 40. (New) The method of claim 39, wherein the high-frequency-pulsed high-frequency power is pulsed at a frequency of 50 kHz to 200 kHz.
- 41. (New) The method of claim 38, wherein the high-frequency carrier signal has a frequency of 1 MHz to 50 MHz.
- 42. (New) The method of claim 41, wherein the high-frequency carri r signal has a frequency of 13.56 MHz.

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- 43. (New) The m thod of claim 38, wherein the high-frequency g nerator generates a high-frequency power having an amplitude of 30 watts to 1200 watts.
- 44. (New) The method of claim 43, wherein the high-frequency generator generates a high-frequency power having an amplitude of 50 watts to 500 watts.
- 45. (New) The method of claim 36, wherein the high-frequency-pulsed high-frequency power is coupled in the form of square-wave pulses.
- 46. (New) The method of claim 36, wherein a mark-to-space ratio of the high-frequency-pulsed high-frequency power is between 1:1 and 1:100.
- 47. (New) The method of claim 46, wherein the mark-to-space ratio of the high-frequency-pulsed high-frequency power is between 1:2 and 1:19.
- 48. (New) The method of claim 36, wherein a sequence of pulses of the high-frequency-pulsed power and pulse intervals corresponds to an average high-frequency power of 1 watt to 100 watts.
- 49. (New) The method of claim 36, wherein the coupled, high-frequency-pulsed high-frequency power is periodically modulated using a low-frequency clocking.
- 50. (New) The method of claim 36, wherein one of a low-frequency clocking and the low-frequency modulation is performed at a frequency of 10 Hz to 10000 Hz.
- 51. (New) The method of claim 50, wherein the one of the low-frequency clocking and the low-frequency modulation is performed at a frequency of 50 Hz to 1000 Hz.
- 52. (New) The method of claim 36, whirein on of a low-frequency clocking and the low-frequency modulation causes the couplid, high-frequency-pulsid high-frequency power to be periodically switched on and off.

- 53. (New) The method of cl. im 36, wherein a mark-to-space ratio of a low-frequency clocking is between 4:1 and 1:4.
- 54. (New) The method of claim 53, wherein the mark-to-space ratio of the low-frequency clocking is between 1:2 and 2:1.